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Publication Year: 2012 , Page(s): 146 - 151
IEEE JOURNALS & MAGAZINES
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Digital Object Identifier: [10.1109/TDMR.2012.2192440](#)
Publication Year: 2012 , Page(s): 437 - 444
IEEE JOURNALS & MAGAZINES
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Wen-Yi Chen; Ming-Dou Ker
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2187450](#)
Publication Year: 2012 , Page(s): 382 - 390
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1265 KB)
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[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 8 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2008.923743](#)
Publication Year: 2008 , Page(s): 332 - 343
[Cited by 61](#)
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Su-Tsai Lu; Jing-Ye Juang; Hsien-Chie Cheng; Yu-Ming Tsai; Tai-Hong Chen; Wen-Hwa Chen
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2187449](#)
Publication Year: 2012 , Page(s): 296 - 305
IEEE JOURNALS & MAGAZINES
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Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2188802](#)
Publication Year: 2012 , Page(s): 194 - 200
IEEE JOURNALS & MAGAZINES
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Sukharev, V.; Kteyan, A.; Zschech, E.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2190605](#)
Publication Year: 2012 , Page(s): 272 - 284
IEEE JOURNALS & MAGAZINES
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Xi Liu; Qiao Chen; Sundaram, V.; Simmons-Matthews, M.; Wachtler, K.P.; Tummala, R.R.; Sitaraman, S.K.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2194495](#)
Publication Year: 2012 , Page(s): 263 - 271
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1236 KB)
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Yan Li; Moore, J.S.; Pathangey, B.; Dias, R.C.; Goyal, D.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2190736](#)
Publication Year: 2012 , Page(s): 494 - 500
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (798 KB)
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Jiajie Fan; Kam-Chuen Yung; Pecht, M.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2190415](#)
Publication Year: 2012 , Page(s): 470 - 477
IEEE JOURNALS & MAGAZINES
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Ming-Dou Ker; Po-Yen Chiu
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 11 , Issue: 3
Digital Object Identifier: [10.1109/TDMR.2010.2066976](#)
Publication Year: 2011 , Page(s): 474 - 483
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1579 KB)
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[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2189402](#)
Publication Year: 2012 , Page(s): 428 - 436
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (614 KB)
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Cassidy, C.; Kraft, J.; Carniello, S.; Roger, F.; Ceric, H.; Singulani, A.P.; Langer, E.; Schrank, F.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2189212](#)
Publication Year: 2012 , Page(s): 285 - 295
IEEE JOURNALS & MAGAZINES
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Suk-Kyu Ryu; Kuan-Hsun Lu; Tengfei Jiang; Jang-Hi Im; Rui Huang; Ho, P.S.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2194784](#)
Publication Year: 2012 , Page(s): 255 - 262
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (782 KB)
- [. Overview on ESD Protection Designs of Low-Parasitic Capacitance for RF ICs in CMOS Technologies](#) 


Ming-Dou Ker; Chun-Yu Lin; Yuan-Wen Hsiao
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 11 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2011.2106129](#)
Publication Year: 2011 , Page(s): 207 - 218
[Cited by 2](#)
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1339 KB)


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En Xia Zhang; Cher Xuan Zhang; Fleetwod, D.M.; Schrimpf, R.D.; Dhar, S.; Sei-Hyung Ryu; Xiao Shen; Pantelides, S.T.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2188404](#)
Publication Year: 2012 , Page(s): 391 - 398
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (511 KB)
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Cheng-Ta Ko; Zhi-Cheng Hsiao; Yao-Jen Chang; Peng-Shu Chen; Yu-Jiau Hwang; Huan-Chun Fu; Jui-Hsiung Huang; Chia-Wen Chiang; Shyh-Shyuan Sheu; Yu-Hua Chen; Wei-Chung Lo; Kuan-Neng Chen
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2195005](#)
Publication Year: 2012 , Page(s): 209 - 216
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1228 KB)
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Chung-Yuan Lee; Chao-Sung Lai; Chia-Ming Yang; Wang, D.H.-L.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2188895](#)
Publication Year: 2012 , Page(s): 406 - 412
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (934 KB)
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Yunhan Huang; Vasani, A.S.S.; Doraiswami, R.; Osterman, M.; Pecht, M.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2191291](#)
Publication Year: 2012 , Page(s): 482 - 493
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (591 KB)
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Xiaojun Li; Jin Qin; Bing Huang; Xiaohu Zhang; Bernstein, J.B.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 6 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2006.876572](#)
Publication Year: 2006 , Page(s): 247 - 257
[Cited by 12](#)
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (384 KB)
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Tambat, A.; Hung-Yun Lin; Subbarayan, G.; Dae Young Jung; Sammakia, B.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2195006](#)
Publication Year: 2012 , Page(s): 241 - 254
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1341 KB)
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Ribes, G.; Mitard, J.; Denais, M.; Bruyere, S.; Monsieur, F.; Parthasarathy, C.; Vincent, E.; Ghibaud, G.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 5 , Issue: 1
Digital Object Identifier: [10.1109/TDMR.2005.845236](#)
Publication Year: 2005 , Page(s): 5 - 19
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IEEE JOURNALS & MAGAZINES
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Karmarkar, A.P.; Xiaopeng Xu; Kong-Boon Yeap; Zschech, E.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2189401](#)
Publication Year: 2012 , Page(s): 225 - 232
IEEE JOURNALS & MAGAZINES
[Quick Abstract](#) | [PDF](#) (1019 KB)
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Rong Zhang; Lo, J.C.C.; Lee, S.W.R.
[Device and Materials Reliability, IEEE Transactions on](#)
Volume: 12 , Issue: 2
Digital Object Identifier: [10.1109/TDMR.2012.2190764](#)
Publication Year: 2012 , Page(s): 189 - 193
IEEE JOURNALS & MAGAZINES
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